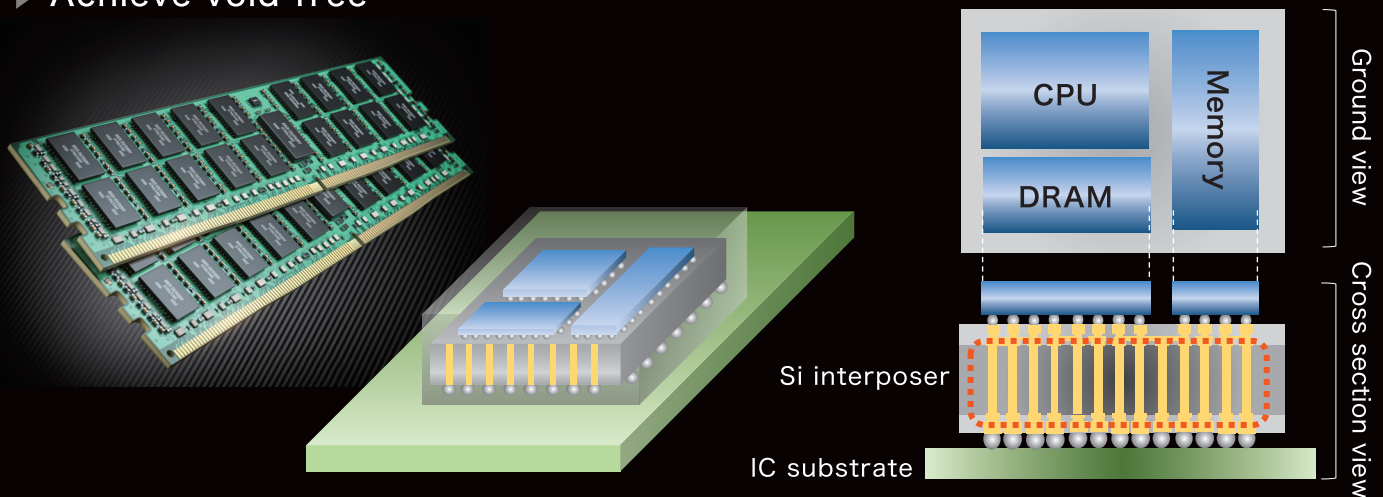


Acid copper plating additive to silicon interposer for high aspect ratio filling

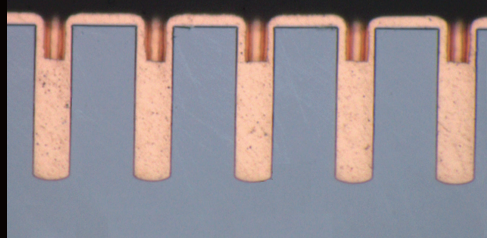
TORYZA LCN SV

- ▶ Realize high aspect ratio filling by small thickness
- ▶ Achieve void free



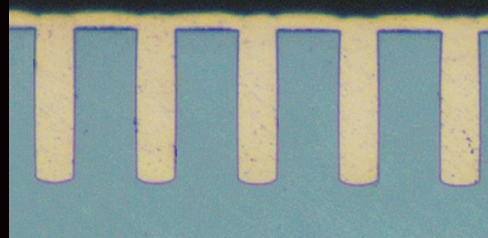
High aspect filling by small thickness

Seed layer + Surface thickness
2.05 μm



Plating time : 15min

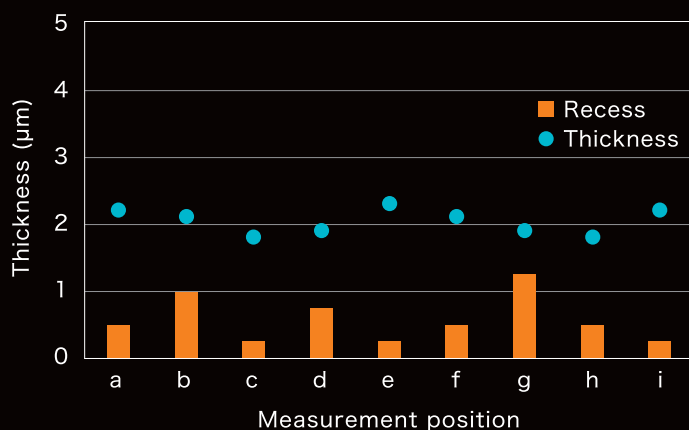
Seed layer+Surface thickness
2.73 μm



Plating time : 30min

Current density: 0.2A/dm² Via diameter: 7 μm Via depth: 25 μm

Excellent in filling performance into TGV



Sampling points

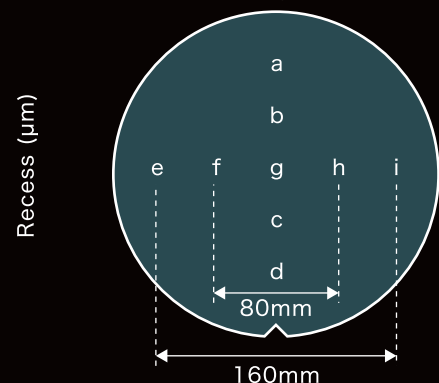


Image of wafer and measurement position